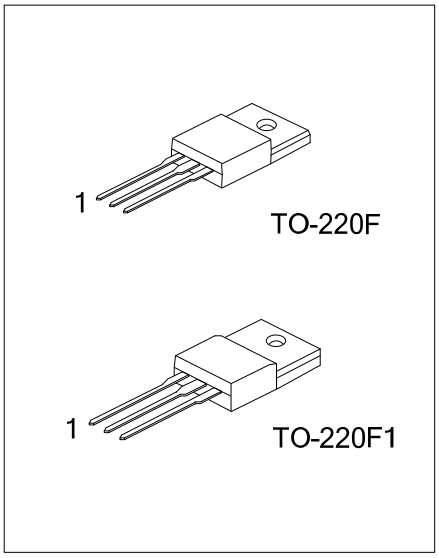
10N70K-MT

Power MOSFET

10A, 700V N-CHANNEL POWER MOSFET



■ DESCRIPTION

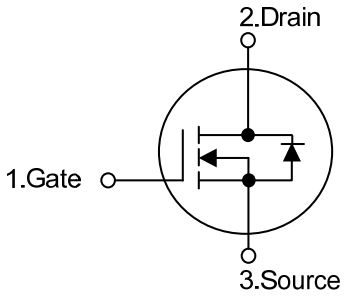
The UTC **10N70K-MT** is an N-channel Power MOSFET using UTC's advanced technology to provide customers a minimum on-state resistance and superior switching performance, etc.

The UTC **10N70K-MT** is generally applied in high efficient DC to DC converters, PWM motor controls and bridge circuits, etc.

■ FEATURES

* $R_{DS(ON)}$< 1.08Ω @ V_{GS} = 10V, I_D = 5.0A
* High Switching Speed
* Improved dv/dt capability

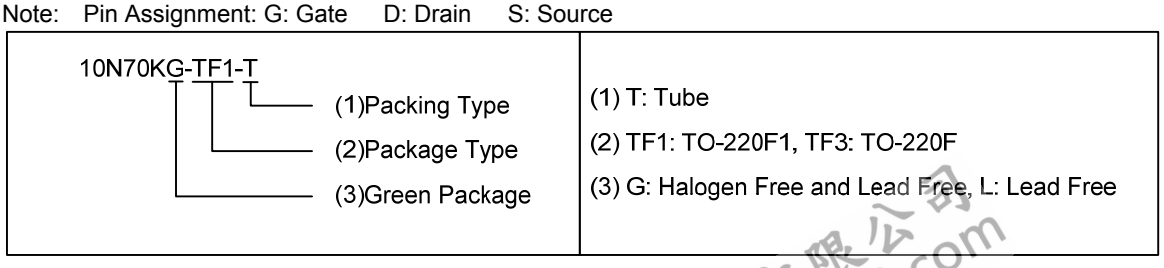
■ SYMBOL



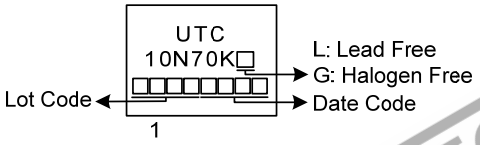
■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
10N70KL-TF1-T	10N70KG-TF1-T	TO-220F1	G	D	S	Tube
10N70KL-TF3-T	10N70KG-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source



■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	10	A
	Pulsed (Note 2)	I_{DM}	20	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	252	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.3	V/ns
Power Dissipation		P_D	50	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L = 30mH, I_{AS} = 4.1A, V_{DD} = 50V, R_G = 25 Ω Starting T_J = 25°C
4. I_{SD} ≤ 10A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J = 25°C

■ THERMAL DATA

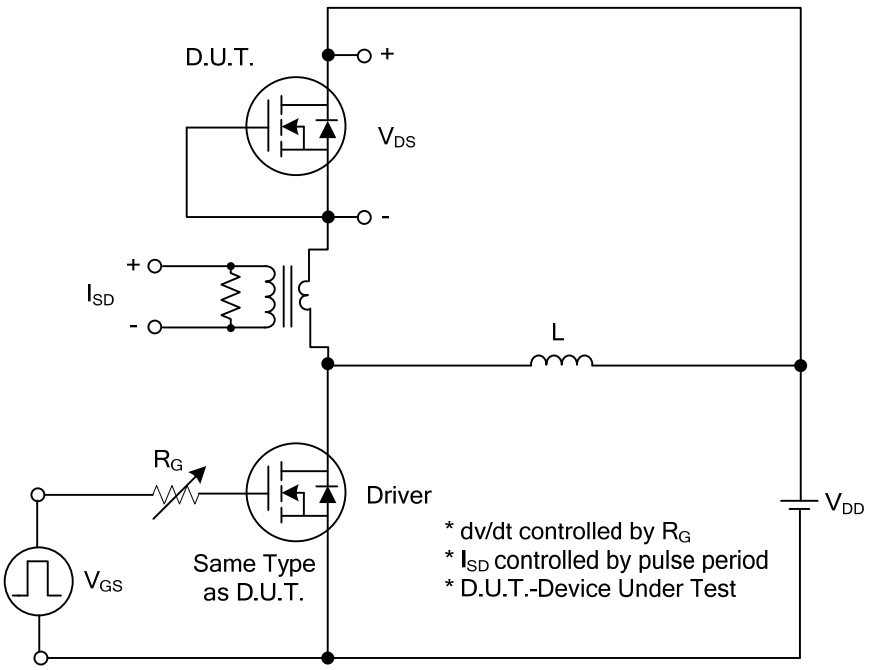
PARAMETER	SYMBOL	RATING	UNIT
Junction to Ambient	$θ_{JA}$	62.5	°C/W
Junction to Case	$θ_{JC}$	2.5	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

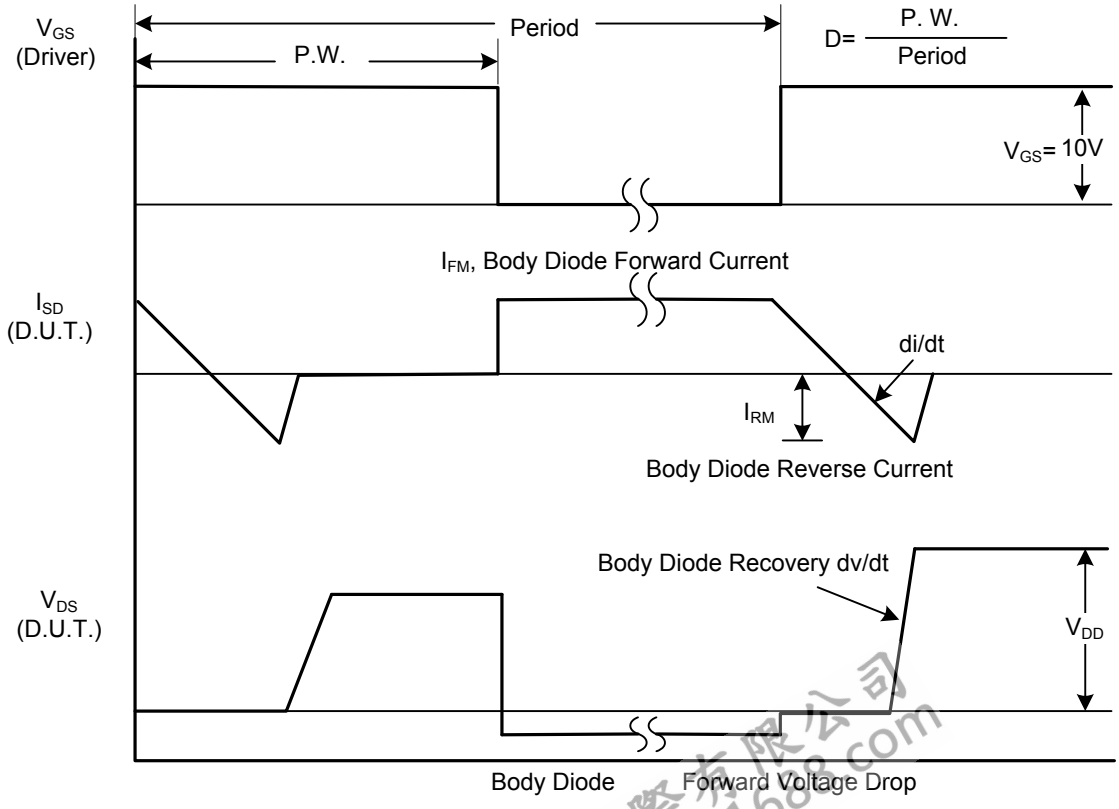
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D= 250μA	700			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=700V, V_{GS}=0V			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{GS}=30V, V_{DS}=0V			100	nA
	Reverse		V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=5.0A			1.08	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	V_{GS}=0V, V_{DS}=25V, f=1.0MHz		1450		pF
Output Capacitance		C_{OSS}			130		pF
Reverse Transfer Capacitance		C_{RSS}			60		pF
SWITCHING CHARACTERISTICS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=300V, V_{GS}=10V, I_D=10A I_G=3mA (Note 1, 2)		34		nC
Gateource Charge		Q_{GS}			11		nC
Gate-Drain Charge		Q_{GD}			7.6		nC
Turn-on Delay Time (Note 1)		$t_{D(ON)}$	V_{DS}=300V, V_{GS}=10V, I_D=10A, R_G=25Ω (Note 1, 2)		19		ns
Rise Time		t_R			21		ns
Turn-off Delay Time		$t_{D(OFF)}$			102		ns
Fall-Time		t_F			30		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				10	A
Maximum Body-Diode Pulsed Current		I_{SM}				20	A
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	V_{GS}=0V, I_S=10A			1.4	V
Reverse Recovery Time (Note 1)		t_{rr}	V_{GS}=0V, I_S=10A, dI_F/dt=100A/μs (Note1)		390		ns
Reverse Recovery Charge		Q_{rr}			4.6		μC

Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

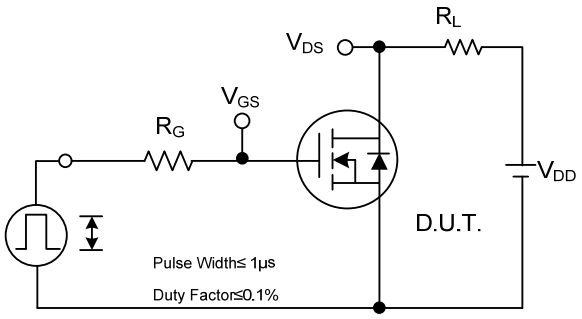


Peak Diode Recovery dv/dt Test Circuit

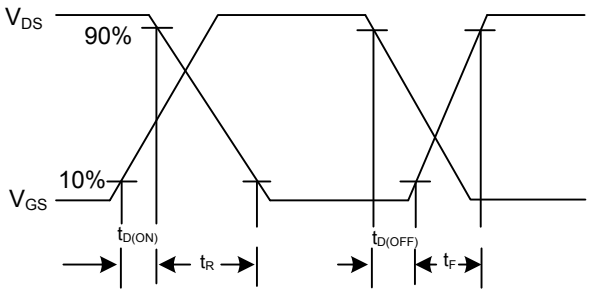


Peak Diode Recovery dv/dt Waveforms

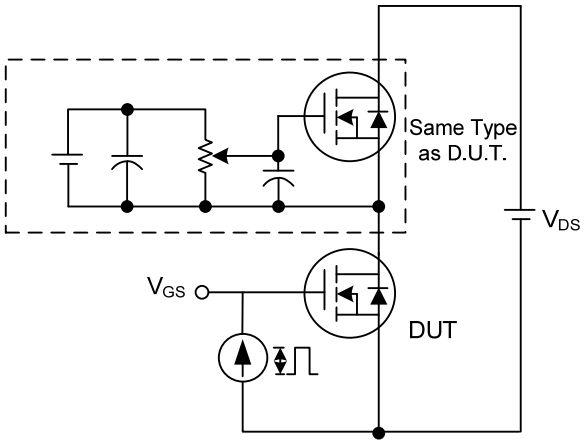
■ TEST CIRCUITS AND WAVEFORMS



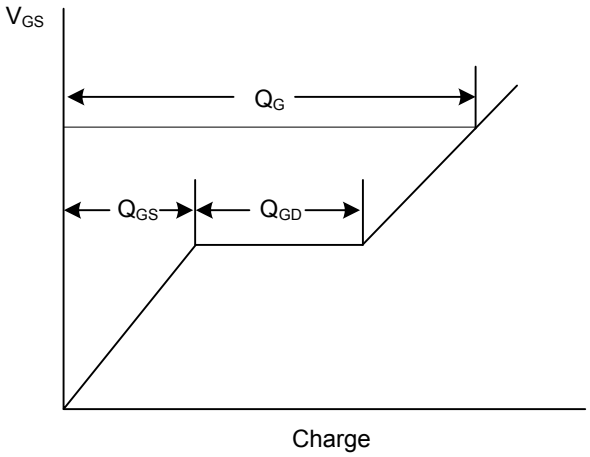
Switching Test Circuit



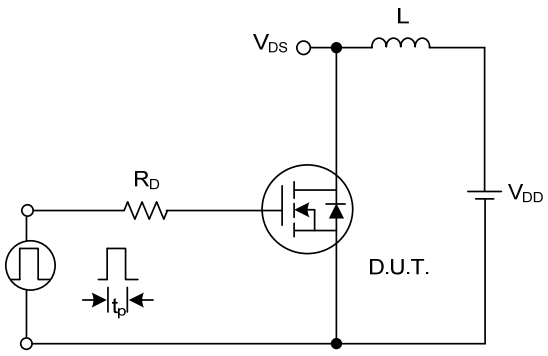
Switching Waveforms



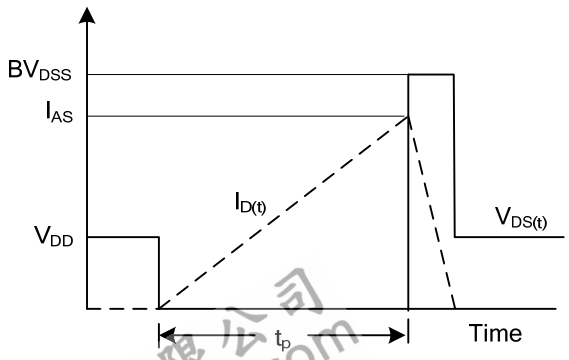
Gate Charge Test Circuit



Gate Charge Waveform



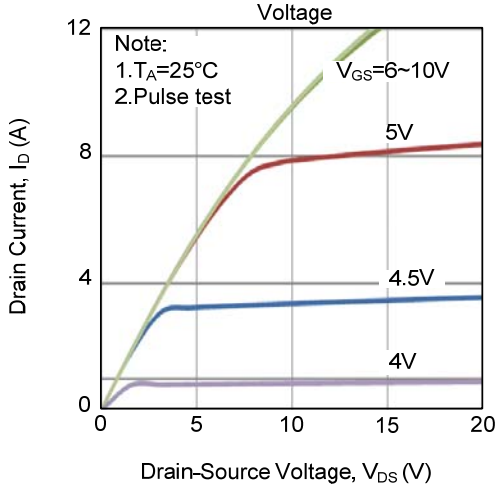
Unclamped Inductive Switching Test Circuit



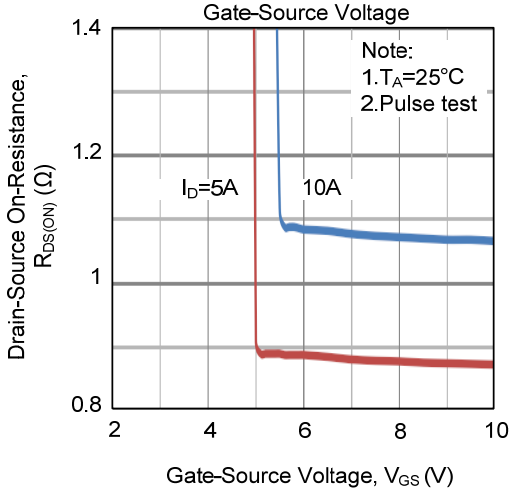
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

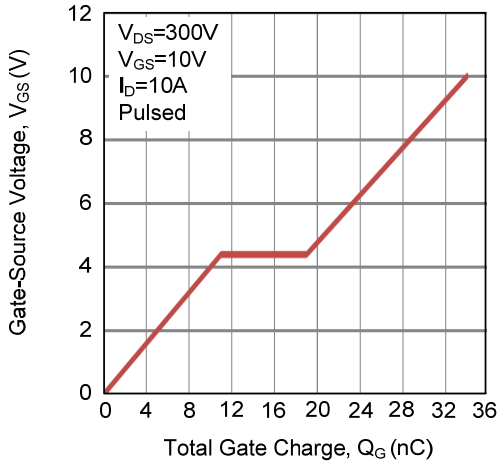
Drain Current vs. Drain-Source Voltage



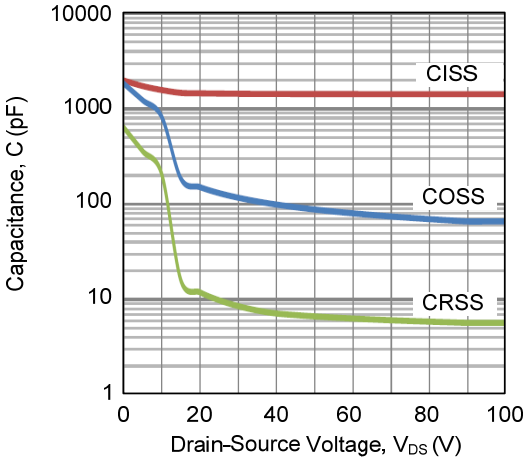
Drain-Source On-Resistance vs. Gate-Source Voltage



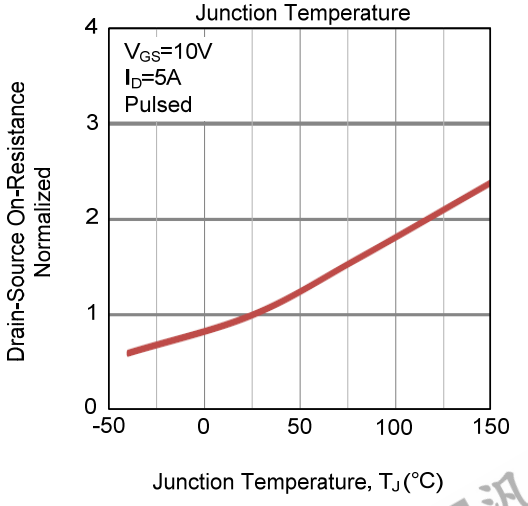
Gate Charge Characteristics



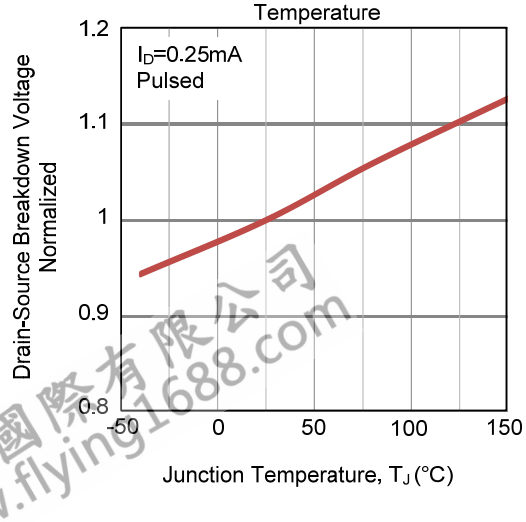
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

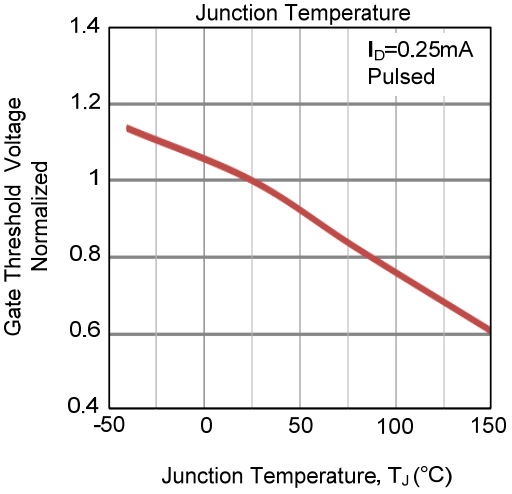


Breakdown Voltage vs. Junction Temperature

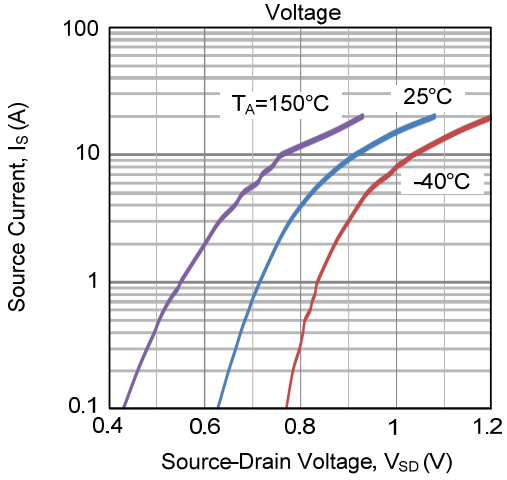


■ TYPICAL CHARACTERISTICS (Cont.)

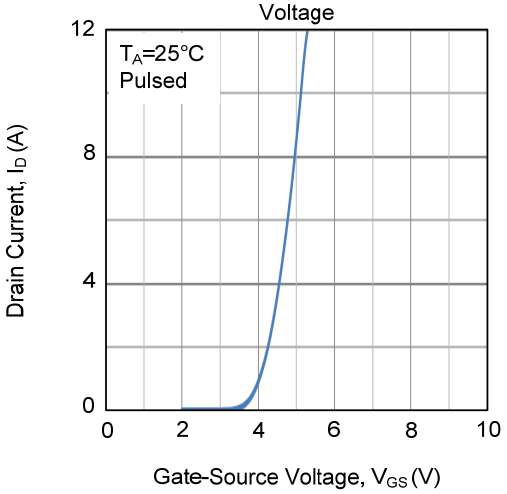
Gate Threshold Voltage vs. Junction Temperature



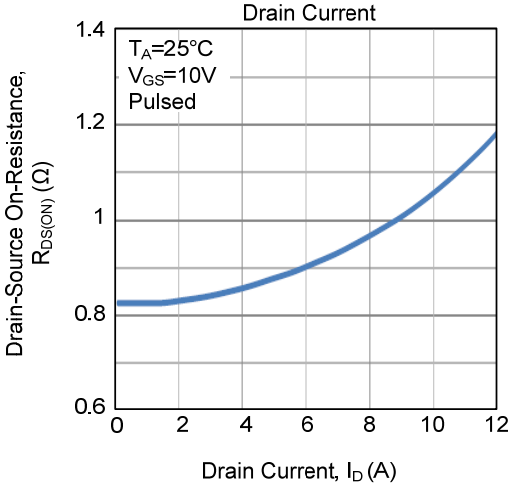
Source Current vs. Source-Drain Voltage



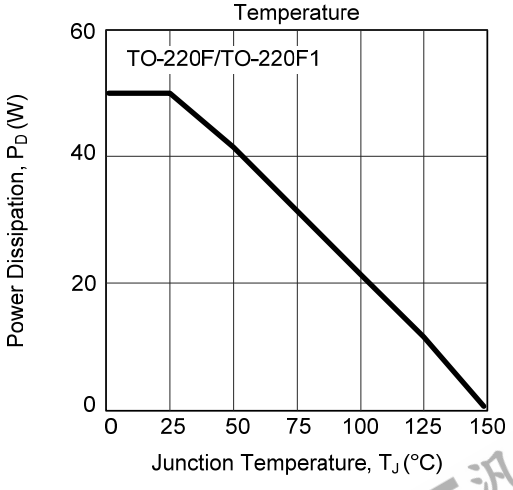
Drain Current vs. Gate-Source Voltage



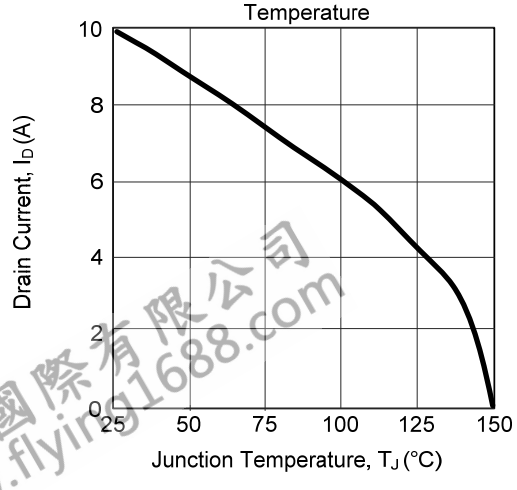
Drain-Source On-Resistance vs. Drain Current



Power Dissipation vs. Junction Temperature



Drain Current vs. Junction Temperature



■ TYPICAL CHARACTERISTICS (Cont.)